



PNP GENERAL PURPOSE TRANSISTORS

VOLTAGE 30/45/65 Volts POWER 330 mWatts

FEATURES

- General Purpose Amplifier Applications
- Collector Current IC = -100mA
- Complimentary (PNP) Devices: BC846/BC847/BC848/BC849 Series
- \eth Lead free in comply with EU RoHS 2002/95/EC directives.
- ð Green molding compound as per IEC61249 Std. . (Halogen Free)

MECHANICAL DATA

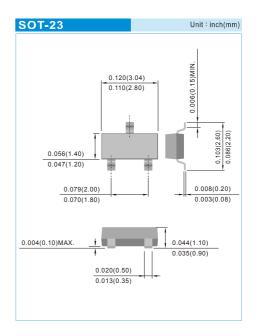
Case: SOT-23

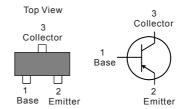
Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.008 gram

Marking:

Device Marking:							
BC856A=56A	BC857A=57A	BC858A=58A					
BC856B=56B	BC857B=57B	BC858B=58B	BC859B=59B				
	BC857C=57C	BC858C=58C	BC859C=59C				





ABSOLUTE RATINGS

PARAMETER	Symbol	BC856	BC857	BC858	BC859	Units		
Collector - Emitter Voltage	VCEO	-65	-45 -30		V			
Collector - Base Voltage	Vсво	-80	-50	-30		-30		V
Emitter - Base Voltage	VEBO	-5			V			
Collector Current - Continuous	Ic	-100		mA				
Max Power Dissipation(Note1)		330			mW			
Typical Thermal Resistance, Junction to Ambient	Rөja	375		°C/W				
Operating Junction and Storage Temperature Range		-50 to 150			°C			

NOTES:

1. Transistor mounted on FR-4 board 8 cm².

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ELECTRICAL CHARACTERISTICS

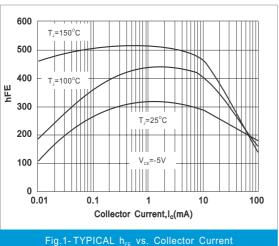
PARAMETER		Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	BC856A,B BC857A,B,C BC858A,B,C,BC859B,C	V _(BR) CEO	Ic=-10mA, Is=0	-65 -45 -30	-	-	V
Collector - Base Breakdown Voltage	BC856A,B BC857A,B,C BC858A,B,C,BC859B,C	V _(BR) CBO	Ic=-10μA, Iε=0	-80 -50 -30	-	-	V
Emitter - Base Breakdown Voltage		V _(BR) EBO	IE=-1.0μA, IC=0	-5.0	-	-	٧
Emitter-Base Cutoff Current		Ієво	VEB=-5V	-	-	-100	nA
Collector-Base Cutoff Current		Ісво	VcB=-30V, IE=0 VcB=-30V, IE=0,TJ=150°C	-	-	-15 -4.0	nA μA
DC Current Gain	BC856A,BC857A,BC858A BC856B,BC857B,BC858B,BC859B BC857C,BC858C,BC859C	h _{FE}	Ic=-10μA, Vcε=-5V	-	90 150 270	-	-
DC Current Gain	BC856A,BC857A,BC858A BC856B,BC857B,BC858B,BC859B BC857C,BC858C,BC859C	h _{FE}	Ic=-2.0mA, VcE=-5V	110 220 420	180 290 520	220 475 800	-
Collector - Emitter Saturation Voltage		VCE(SAT)	Ic=-10mA, IB=-0.5mA Ic=-100mA, IB=-5.0mA	-	-	-0.3 -0.65	٧
Base - Emitter Saturation Voltage		VBE(SAT)	Ic=-10mA, IB=-0.5mA Ic=-100mA, IB=-5.0mA	-	-0.7 -0.9	-	V
Base - Emitter On Voltage		VBE(ON)	IC=-2mA, VCE=-5.0V IC=-10mA, VCE=-5.0V	-0.60 -	-	-0.75 -0.82	٧
Collector - Base Capacitance		Ссв	VcB=-10V, IE=0, f=1MH	-	-	4.5	pF
Current-Gain-Bandwidth Product		Fī	Ic=-10mA, VcE=-5.0V,f=100MHz	-	200	-	MHz

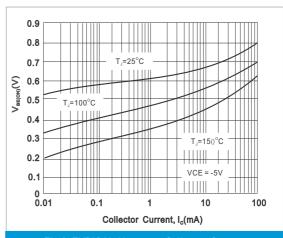
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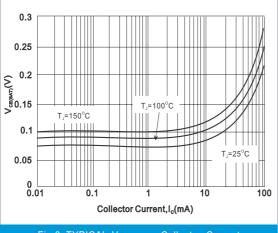




ELECTRICAL CHARACTERISTICS CURVES







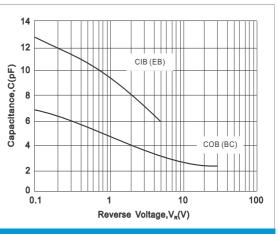


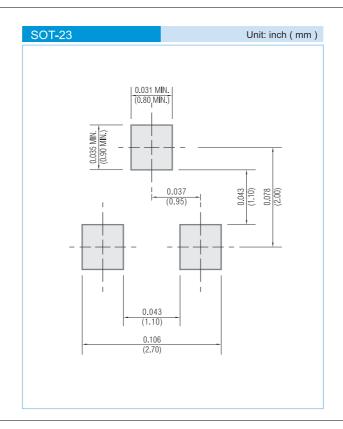
Fig.4-TYPICAL CAPACITANCES vs. REVERSE VOLTAGE

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MOUNTING PAD LAYOUT



ORDER INFORMATION

Packing information

T/R - 12K per 13" plastic Reel

T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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